**IN THE CLAIMS:**

1. **(Currently Amended)** An electronic device, comprising:

a substrate;

a lower conductive film formed on said substrate, **said lower conductive film being a metallic film oriented in a (111) plane of a face-centered cubic structure or a (0001) plane of a hexagonal close-packed structure**; and

a functional film formed on said lower conductive film, **said functional film being made of a piezoelectric material having a wurtzite crystal structure**,

wherein adhesion of said lower conductive film on a side of said substrate is greater than or equal to 0.1 N/cm.

2-4. **(Canceled)**

5. **(Original)** The electronic device as claimed in claim 1, further comprising an adhesion orientation control film provided between said substrate and said lower conductive film.

6-8. **(Canceled)**

9. **(Original)** Then electronic device as claimed in claim 5, wherein said adhesion orientation control film is made of a crystal having a wurtzite structure.

10. **(Original)** The electronic device as claimed in claim 9, wherein said adhesion orientation control film is a (0001)-oriented film whose (0001) plane is oriented parallel to a surface of said substrate.

11. **(Currently Amended)** The electronic device as claimed in ~~claim 9~~ claim 5, wherein said adhesion orientation control film is made of AlN.

12. **(Canceled)**

13. **(Original)** The electronic device as claimed in claim 1, wherein a X-ray rocking curve FWHM of said lower conductive film and functional film are less than or equal to 5 degrees.

14. **(Canceled)**

15. **(Original)** The electronic device as claimed in claim 1, further comprising an upper conductive film provided on said functional film, thereby configuring a film bulk acoustic wave resonator composed of said lower conductive film, functional film and upper conductive film.

16. **(Original)** The electronic device as claimed in claim 15, wherein said substrate includes an acoustic multilayer at its surface.

17-22. **(Cancelled)**

23. **(New)** An electronic device, comprising:

a substrate;

a lower conductive film formed on said substrate, said lower conductive film being a metallic film oriented in a (111) plane of a face-centered cubic structure or a (0001) plane of a hexagonal close-packed structure; and

a functional film formed on said lower conductive film, said functional film is made of a piezoelectric material having a wurtzite crystal structure,

wherein adhesion of said lower conductive film on a side of said substrate is greater than or equal to 1 N/cm.

24. **(New)** The electronic device as claimed in claim 23, wherein a X-ray rocking curve FWHM of said lower conductive film and functional film are less than or equal to 5 degrees.

25. **(New)** The electronic device as claimed in claim 23, further comprising an upper conductive film provided on said functional film, thereby configuring a film bulk acoustic wave resonator composed of said lower conductive film, functional film and upper conductive film.

26. **(New)** The electronic device as claimed in claim 25, wherein said substrate includes an acoustic multilayer at its surface.

27. **(New)** An electronic device, comprising:

a substrate;

a lower conductive film formed on said substrate;

an adhesion orientation control film provided between said substrate and said lower conductive film, said adhesion orientation control film being made of a crystal having a wurtzite structure, and

a functional film formed on said lower conductive film,

wherein adhesion of said lower conductive film on a side of said substrate is greater than or equal to 0.1 N/cm.

28. **(New)** The electronic device as claimed in claim 27, wherein said adhesion orientation control film is made of AlN.

29. (New) An electronic device, comprising:

a substrate;

a lower conductive film formed on said substrate; and

a functional film formed on said lower conductive film, an X-ray rocking curve FWHM of said lower conductive film and functional film being less than or equal to 5 degrees,

wherein adhesion of said lower conductive film on a side of said substrate is greater than or equal to 0.1 N/cm.

30. (New) The electronic device as claimed in claim 29, wherein said X-ray rocking curve FWHM of said lower conductive film and functional film are less than or equal to 3 degrees.

31. (New) The electronic device as claimed in claim 29, further comprising an upper conductive film provided on said functional film, thereby configuring a film bulk acoustic wave resonator composed of said lower conductive film, functional film and upper conductive film.

32. (New) The electronic device as claimed in claim 31, wherein said substrate includes an acoustic multilayer at its surface.

33. (New) An electronic device, comprising:

a substrate;

a lower conductive film formed on said substrate;

a functional film formed on said lower conductive film, and

an upper conductive film provided on said functional film, thereby configuring a film bulk acoustic wave resonator composed of said lower conductive film, functional film and upper conductive film,

wherein adhesion of said lower conductive film on a side of said substrate is greater than or equal to 0.1 N/cm.

34. **(New)** The electronic device as claimed in claim 33, wherein said substrate includes an acoustic multilayer at its surface.